CLAIMS

{Claim 1}

A thermally conductive film-like adhesive comprising:

an epoxy resin (A);

an epoxy resin curing agent (B);

a polymer component (C); and

an inorganic filler (D),

wherein a capillary rheometer viscosity at a temperature of 120°C and a load of 20 Kg is 1 to 1000 Pa·s,

wherein a detection time of an exothermic peak in differential scanning calorimetry that performs holding at 120°C is 15 minutes or longer,

wherein the epoxy resin curing agent (B) contains an imidazole compound,

wherein a content of the epoxy resin curing agent (B) per 100 parts by mass of the epoxy resin (A) is 1 to 6 parts by mass, and

wherein the inorganic filler (D) has a sphericity of 0.6 to 1.0.

{Claim 2}

The thermally conductive film-like adhesive according to claim 1,

wherein a proportion of the inorganic filler (D) to a total content of the epoxy resin (A), the epoxy resin curing agent (B), the polymer component (C), and the inorganic filler (D) is 30 to 70% by volume, and

wherein a cured product having a thermal conductivity of 1.0 W/m·K or more is provided after thermal curing.

{Claim 3}

The thermally conductive film-like adhesive according to claim 1 or 2,

having a thickness of 1 to 20 μm.

{Claim 4}

A dicing die attach film obtained by stacking a dicing film and the thermally conductive film-like adhesive according to any one of claims 1 to 3.

{Claim 5}

A method of producing a semiconductor package, comprising:

a first step of thermocompression-bonding the thermally conductive film-like adhesive according to any one of claims 1 to 3 to a back surface of a semiconductor wafer in which at least one semiconductor circuit is formed on a surface, and providing a dicing film via a layer of the thermally conductive film-like adhesive;

a second step of integrally dicing the semiconductor wafer and an adhesive layer to obtain a semiconductor chip with the adhesive layer on the dicing film;

a third step of removing the dicing film from the adhesive layer and thermocompression-bonding the semiconductor chip with the adhesive layer and a wiring board via the adhesive layer; and

a fourth step of thermally curing the adhesive layer.

{Claim 6}

The method of producing a semiconductor package according to claim 5, wherein the first step is a step of thermocompression-bonding the dicing die attach film according to claim 4 to a back surface of the semiconductor wafer.

{Claim 7}

The method of producing a semiconductor package according to claim 5 or 6, wherein the thermally curing in the fourth step is performed in a pressure

oven set at 100 to 150°C.

{Claim 8}

A semiconductor package obtained by the producing method according to any one of claims 5 to 7.